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	Application No.	Applicant(s)	
Notice of Allowability	10/633,201	KORENEV ET AL.	
Notice of Anowability	Examiner	Art Unit	
·	Roberts Culbert	1763	
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) of NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIC of the Office or upon petition by the applicant. See 37 CFR 1.313	OR REMAINS) CLOSED in this apport of the properties of the propert	plication. If not included will be mailed in due course. THIS	
1. This communication is responsive to the amendment filed 8	<u>/22/05</u> .		
2. The allowed claim(s) is/are <u>6-11,13 and 15-26</u> .			
 3. Acknowledgment is made of a claim for foreign priority und a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 	been received.		
 Copies of the certified copies of the priority door International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 	uments have been received in this	national stage application from the	
Applicant has THREE MONTHS FROM THE "MAILING DATE" on noted below. Failure to timely comply will result in ABANDONME THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	f this communication to file a reply ENT of this application.	complying with the requirements	
4. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which gives	ted. Note the attached EXAMINER sreason(s) why the oath or declara	S AMENDMENT or NOTICE OF tion is deficient.	
 5. ☐ CORRECTED DRAWINGS (as "replacement sheets") must (a) ☐ including changes required by the Notice of Draftsperso 1) ☐ hereto or 2) ☐ to Paper No./Mail Date (b) ☐ including changes required by the attached Examiner's 	on's Patent Drawing Review (PTO-		
Paper No /Mail Date Identifying indicia such as the application number (see 37 CFR 1.8 each sheet. Replacement sheet(s) should be labeled as such in the	4(c)) should be written on the drawin	ngs in the front (not the back) of	
DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT F	it of BIOLOGICAL MATERIAL n	nust be submitted. Note the	
Attachment(s) 1. ☐ Notice of References Cited (PTO-892)	5. ☐ Notice of Informal Pa	atent Application (PTO-152)	
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. Interview Summary Paper No /Mail Date	6. Interview Summary (PTO-413), Paper No./Mail Date	
3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/08), 7. ☐ Examiner's A		mendment/Comment	
Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. 🛛 Examiner's Stateme	nt of Reasons for Allowance	
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EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Mark Kusner on 8/30/05.

The application has been amended as follows:

1. Cancel Claim 14.

2. Amend Claim 11 to read as follows:

A method of forming a microporous fluoropolymer sheet, comprising the steps of:

irradiating a sheet of fluoropolymer at a dosage level below the rupture energy of the carbon-tofluorine (C-F) bonds of the fluoropolymer, but sufficient to rupture carbon-to-carbon (C-C) bonds; and
exposing the sheet of fluoropolymer to an etchant for a period of time sufficient to etch away
disrupted atoms and molecules, wherein continuous micropassages are formed through said sheet, and
wherein said etchant is fluorine gas.

3. Amend Claim 13 to read as follows:

A method of forming a microporous fluoropolymer sheet, comprising the steps of:

irradiating a sheet of fluoropolymer at a dosage level below the rupture energy of the carbon-tofluorine (C-F) bonds of the fluoropolymer, but sufficient to rupture carbon-to-carbon (C-C) bonds; and
exposing the sheet of fluoropolymer to an etchant for a period of time sufficient to etch away
disrupted atoms and molecules, wherein continuous micropassages are formed through said sheet, and
wherein said sheet of fluoropolymer is one of several sheets simultaneously exposed to said electrons,
and wherein said several sheets of fluoropolymer are layered one on another into a stack and said
electrons radiate through said stack.

Allowable Subject Matter

Claims 6-11, 13, and 15-26 are allowed.

The following is an examiner's statement of reasons for allowance:

The prior art of record fails to teach a method of forming a microporous fluoropolymer sheet, comprising the steps of irradiating a sheet of fluoropolymer at a dosage level below the rupture energy of the carbon-to-fluorine (C-F) bonds of the fluoropolymer, but sufficient to rupture carbon-to-carbon (C-C) bonds by moving the fluoropolymer sheet past a stationary electron source wherein the source of electrons is a target material exposed to x-rays, or an isotope, and exposing the sheet of fluoropolymer to an etchant for a period of time sufficient to etch away disrupted atoms and molecules, wherein continuous micropassages are formed through said sheet as recited in claims 6 and 7.

The prior art of record fails to teach a method of forming a microporous fluoropolymer sheet, comprising the steps of irradiating a sheet of fluoropolymer at a dosage level below the rupture energy of the carbon-to-fluorine (C-F) bonds of the fluoropolymer, but sufficient to rupture carbon-to-carbon (C-C) bonds and exposing the sheet of fluoropolymer to an etchant for a period of time sufficient to etch away disrupted atoms and molecules, wherein continuous micropassages are formed through said sheet, and wherein said etchant is fluorine gas as recited in claim 11.

The prior art of record fails to teach a method of forming a microporous fluoropolymer sheet, comprising the steps of irradiating a sheet of fluoropolymer at a dosage level below the rupture energy of the carbon-to-fluorine (C-F) bonds of the fluoropolymer, but sufficient to rupture carbon-to-carbon (C-C) bonds; and exposing the sheet of fluoropolymer to an etchant for a period of time sufficient to etch away disrupted atoms and molecules, wherein continuous micropassages are formed through said sheet, and wherein said sheet of fluoropolymer is one of several sheets simultaneously exposed to said electrons, and wherein said several sheets of fluoropolymer are layered one on another into a stack and said electrons radiate through said stack as recited in claim 13.

The prior art of record fails to teach a method of forming a microporous fluoropolymer sheet, comprising the steps of irradiating a sheet of fluoropolymer at a dosage level below the rupture energy of the carbon-to-fluorine (C-F) bonds of the fluoropolymer, but sufficient to rupture carbon-to-carbon (C-C) bonds, and exposing the sheet of fluoropolymer to an etchant for a period of time sufficient to etch away disrupted atoms and molecules, wherein continuous micropassages are formed through said sheet, and wherein said irradiated fluoropolymer sheet is etched in a liquid etchant within an electric field that produces an electrophoresis effect in said liquid etchant as recited in claim 15.

The prior art of record fails to teach a method of forming a microporous fluoropolymer sheet, comprising the steps of irradiating a sheet of fluoropolymer at a dosage level below the rupture energy of the carbon-to-fluorine (C-F) bonds of the fluoropolymer, but sufficient to rupture carbon-to-carbon (C-C) bonds, and exposing the sheet of fluoropolymer to an etchant for a period of time sufficient to etch away disrupted atoms and molecules, wherein continuous micropassages are formed through said sheet, and wherein said step of irradiating occurs with an oxygen-bearing medium supplied to an area where said fluoropolymer sheet is irradiated as recited in claim 17.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Roberts Culbert whose telephone number is (571) 272-1433. The examiner can normally be reached on Monday-Friday (8:30-5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Parviz Hassanzadeh can be reached on (571) 272-1435. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Application/Control Number: 10/633,201

Art Unit: 1763

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

R. Culbert

M. Colmit

SUPERVISORY PATENT EXAMINER

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